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January 2009

FDD6778A N-Channel PowerTrench[®] MOSFET

FDD6778A N-Channel PowerTrench[®] MOSFET 25 V, 14.0 m Ω

Features

- Max $r_{DS(on)}$ = 14.0 m Ω at V_{GS} = 10 V, I_D = 10.0 A
- Max $r_{DS(on)}$ = 30.0 m Ω at V_{GS} = 4.5 V, I_D = 9.7 A
- 100% UIL tested
- RoHS Compliant

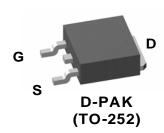


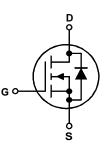
General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $r_{\text{DS}(\text{on})}$ and fast switching speed.

Applications

- Vcore DC-DC for Desktop Computers and Servers
- VRM for Intermediate Bus Architecture





MOSFET Maximum Ratings T_C = 25 °C unless otherwise noted

Symbol	Parameter			Ratings	Units
V _{DS}	Drain to Source Voltage			25	V
V _{GS}	Gate to Source Voltage			±20	V
	Drain Current -Continuous (Package limited)	T _C = 25 °C		10	
	-Continuous (Silicon limited)	T _C = 25 °C		30	•
D	-Continuous	T _A = 25 °C	(Note 1a)	12	Α
	-Pulsed			50	
E _{AS}	Single Pulse Avalanche Energy		(Note 3)	12	mJ
Р	Power Dissipation	T _C = 25 °C		24	w
PD	Power Dissipation	T _A = 25 °C	(Note 1a)	3.7	vv
T _J , T _{STG}	Operating and Storage Junction Temperature R	ange		-55 to +175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	6.2	°C/W
R_{\thetaJA}	Thermal Resistance, Junction to Ambient (Note 1	a) 40	C/W

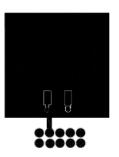
Package Marking and Ordering Information

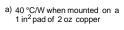
Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDD6778A	FDD6778A	D-PAK (TO-252)	13 "	12 mm	2500 units

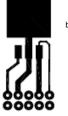
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Chara	acteristics						
BV _{DSS}	Drain to Source Breakdown Voltage	$I_{D} = 250 \ \mu A, V_{GS} = 0 \ V$	25			V	
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, referenced to 25 °C		17		mV/°C	
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 20 V, V _{GS} = 0 V			1	μΑ	
I _{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0 \text{ V}$			±100	nA	
	cteristics			•			
V _{GS(th)}	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250 \ \mu A$ 1.		1.9	3.0	V	
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250 \ \mu\text{A}$, referenced to 25 °C		-6		mV/°C	
r _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10 V, I _D = 10.0 A		11.4	14		
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 9.7 \text{ A}$		22.0	30.0	mΩ	
		$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 10.0 \text{ A}, \text{ T}_{J} = 150 \text{ A}$	°C	17.2	21.2		
9 _{FS}	Forward Transconductance	V _{DS} = 5 V, I _D = 10.0 A		33		S	
-	Characteristics			050	070		
C _{iss}	Input Capacitance	V _{DS} = 13 V, V _{GS} = 0 V,		652	870	pF	
C _{oss}	Output Capacitance Reverse Transfer Capacitance	f = 1 MHz		142 129	190 195	pF pF	
C _{rss}	Gate Resistance			0.8	195	рг	
R _g				0.0		52	
	g Characteristics			6	12	ns	
t _{d(on)}	Rise Time			3	12	ns	
t _r	Turn-Off Delay Time	V_{DD} = 13 V, I _D = 10.0 A, V _{GS} = 10 V, R _{GEN} = 6 Ω		14	26	ns	
t _{d(off)} t _f	Fall Time			2	10	ns	
<u>Կ</u> Q _q	Total Gate Charge	V _{GS} = 0 V to 10 V		12	17	nC	
<u>∝g</u> Q _q	Total Gate Charge	$V_{GS} = 0 V \text{ to } 5 V$ $V_{DD} = 13 V,$		7	10	nC	
Q _{gs}	Gate to Source Charge	$V_{GS} = 0.0103 V$ $V_{DD} = 13 V$, $I_D = 10.0 A$		2.0		nC	
<u>∽gs</u> Q _{gd}	Gate to Drain "Miller" Charge			2.8		nC	

V.	Source to Drain Diode Forward Voltage	$V_{GS} = 0 V, I_S = 3.1 A$ (Note 2)	0.9	1.3	V
V _{SD}	Source to Drain Diode Polward voltage	$V_{GS} = 0 V, I_S = 10.0 A$ (Note 2)	0.8	1.2	v
t _{rr}	Reverse Recovery Time	-I _F = 10.0 A, di/dt = 100 A/μs	14	26	ns
Q _{rr}	Reverse Recovery Charge	$TF = 10.0 \text{ A}, \text{ all at } = 100 \text{ A/}\mu\text{S}$	3	10	nC

Notes: 1: R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{0JC} is guaranteed by design while R_{0JA} is determined by the user's board design.



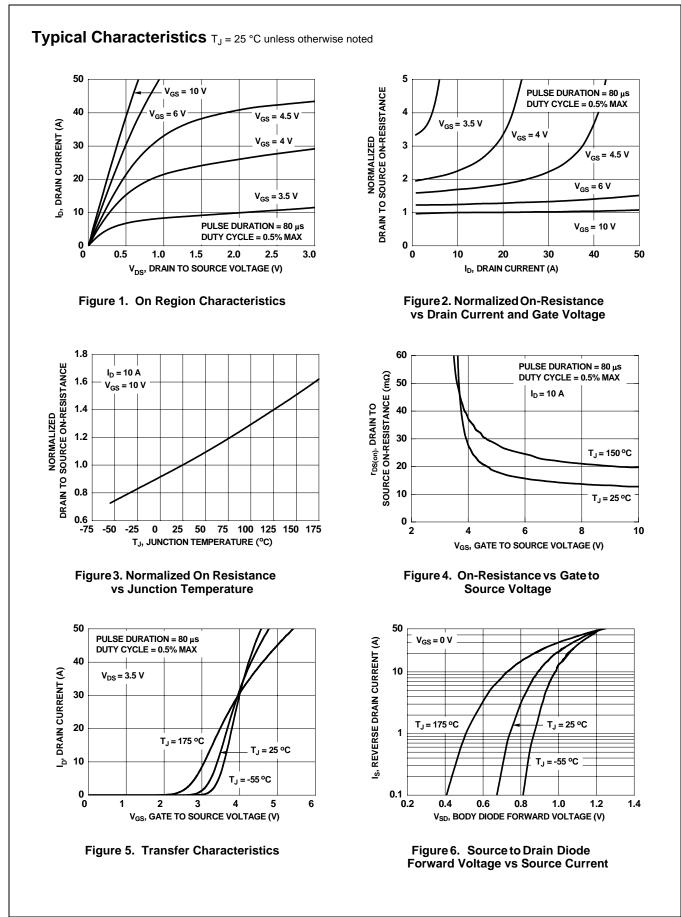


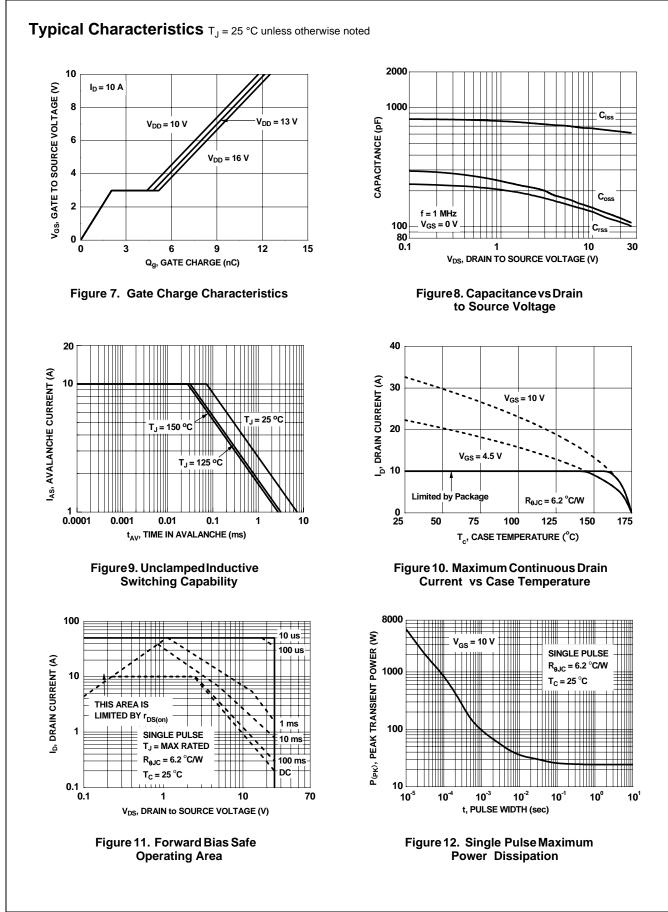


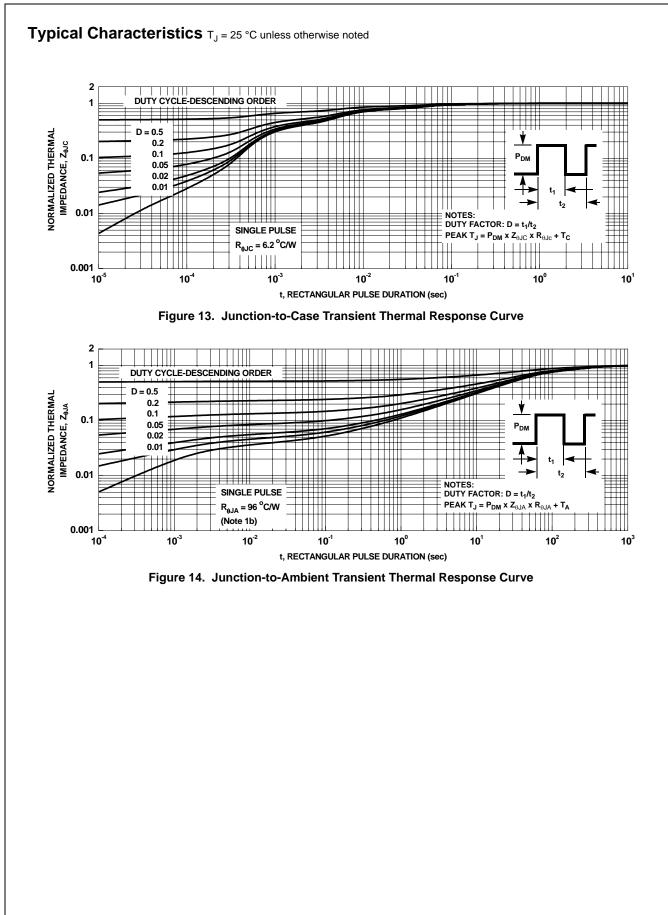
b) 96 °C/W when mounted on a minimum pad

2: Pulse Test: Pulse Width < 300 μ s, Duty cycle < 2.0%. 3: E_{AS} of 12 mJ is based on starting T_J = 25 °C, L = 1 mH, I_{AS} = 5 A, V_{DD} = 23 V, V_{GS} = 10 V. 100% test at L = 0.1 mH, I_{AS} = 12 A.

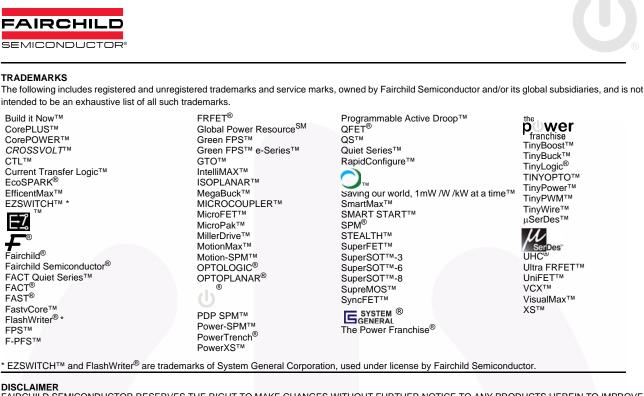
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FDD6778A N-Channel PowerTrench[®] MOSFET



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